

Amendments to the Specification

Please replace the current title with:

A PLANARIZING PROCESS

Examiner is thanked for suggesting this.

Immediately following the title, please insert the following:

This invention is related to application number 10/633,105 filed 08/01/2003

Please replace the second paragraph on page 6 with the following amended paragraph:

The trench in layer 13 is then overfilled with insulating material 14a and planarized so as to be coplanar with 15. Following the deposition and patterning of layers 16 and 17 (write gap and flux concentrator respectively), stitched pole layer 19 is deposited to a thickness between about 1 and 2 microns and cavity 27 is etched therein to define the coil housing area. This cavity has a depth between about 2 and 3 microns, a width between about 20 and 60 microns, and a length between about 6 and 10 microns. After the deposition of protective insulating layer 26 over the entire upper surface the structure has the appearance seen in FIG. 2.

Please replace the second paragraph on page 7 with the following amended paragraph:

Now follows another key feature of the invention. As shown in FIG. 5, the entire structure is covered by alumina layer 52, which is between about 5 and 6 microns thick and which is deposited by sputtering. This is followed by planarization down to the level of lower coil 20. The presence of layer 52 during the final stages of the planarization process serves to stabilize the baked photoresist of layer 14b so that it does not delaminate as the top surface of coil 20 is approached. This makes it

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possible to terminate planarization as soon as the coil is exposed, the end result being as illustrated in FIG. 6.